



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	Ι _D Τ _C = +25°C		
-40V	$11m\Omega$ @ $V_{GS} = -10V$	-35A		
	15mΩ @ V _{GS} = -4.5V	-30A		

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- Backlighting

Features and Benefits

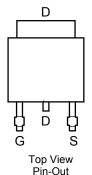
- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

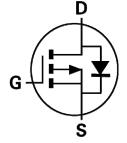
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208³
- Weight: 0.33 grams (approximate)









Equivalent Circuit

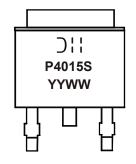
Ordering Information (Note 4)

I	Part Number	Compliance	Case	Packaging
	DMP4015SK3-13	Standard	TO252	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Dil = Manufacturer's Marking
P4015S = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 13 = 2013)
WW = Week (01 - 53)



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	-40	V		
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 5) V _{GS} = -10V	I _D	-35 -27	Α		
Continuous Drain Current (Note EVV - 40V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-14 -11	Α
Continuous Drain Current (Note 5) V _{GS} = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-22 -18	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-100	Α		
Maximum Body Diode Forward Current (Note 5)	I _S	-5.5	Α		
Avalanche Current (Note 6)	I _{AS}	-57	Α		
Avalanche Energy (Note 6)	E _{AS}	162	mJ		

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Dower Dissinction (Note 7)	T _A = +25°C	6	3.5	W
Total Power Dissipation (Note 7)	T _A = +70°C	P _D	2.2	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	D	36	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	15	
Thermal Resistance, Junction to Case (Note 7) Steady state		$R_{ heta JC}$	4.5	
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	-1.5	-2	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D	_	7	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Diain-Source On-Nesistance	R _{DS(ON)}	_	9	15	1112.2	$V_{GS} = -4.5V, I_D = -9.8A$	
Forward Transfer Admittance	Y _{fs}	_	26	_	S	$V_{DS} = -20V, I_{D} = -9.8A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	4234	_		V _{DS} = -20V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	1036	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	526	_		-	
Gate Resistance	R_G	_	7.77	_	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz	
Total Gate Charge	Q_g	_	47.5	_		V _{DS} = -20V, V _{GS} = -5V I _D = -9.8A	
Gate-Source Charge	Q_{gs}	_	14.2	_	nC		
Gate-Drain Charge	Q_{gd}	_	13.5	_		ID = -9.6A	
Turn-On Delay Time	$t_{D(on)}$	_	13.2	_		V _{GS} = -10V, V _{DD} = -20V,	
Turn-On Rise Time	t _r	_	10	_	ns		
Turn-Off Delay Time	$t_{D(off)}$	_	302.7	_	115	$R_G = 6\Omega$, $I_D = -1A$	
Turn-Off Fall Time	t _f		137.9	_			

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. UIS in production with L = 0.1mH, T_J = +25°C.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing. Notes:



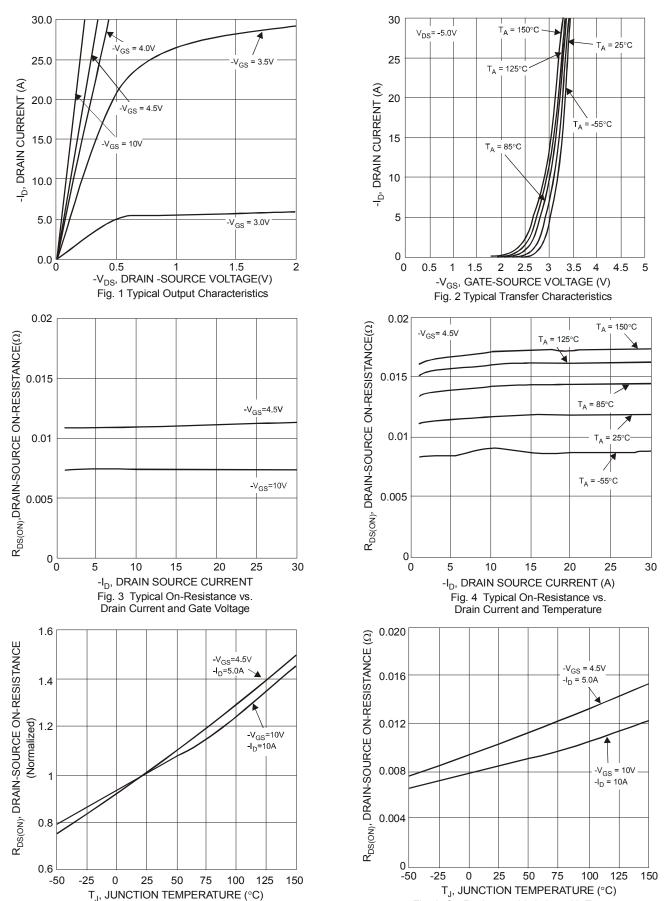


Fig. 5 On-Resistance Variation with Temperature

Fig. 6 On-Resistance Variation with Temperature



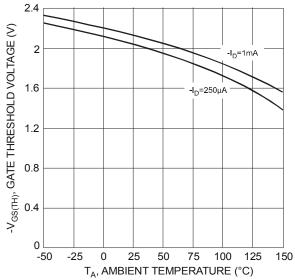
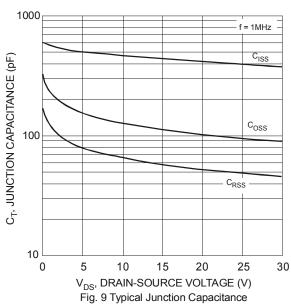
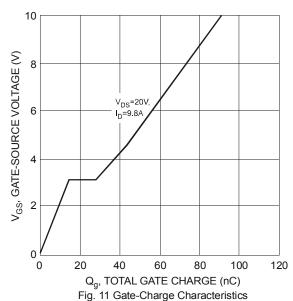
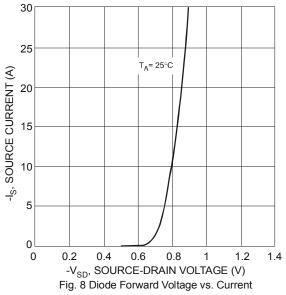


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







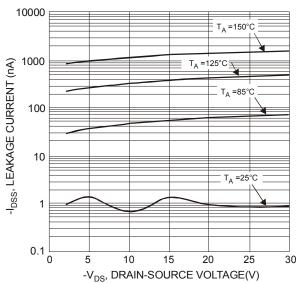


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

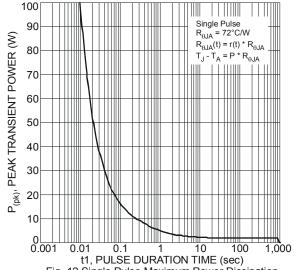
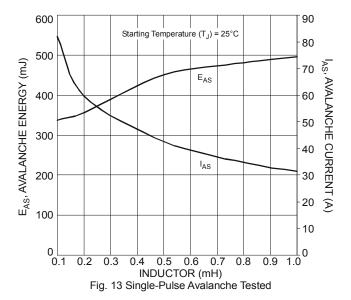
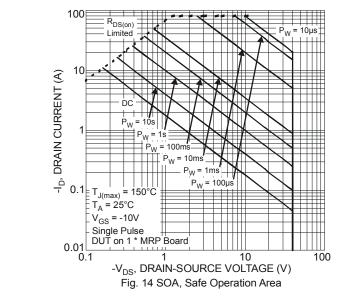
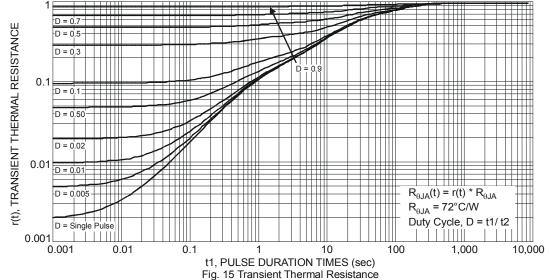


Fig. 12 Single Pulse Maximum Power Dissipation





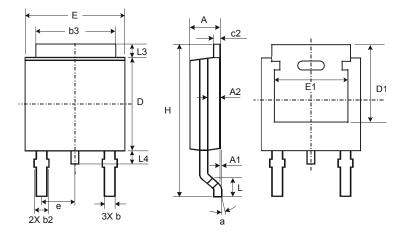






Package Outline Dimensions

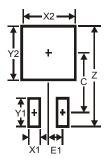
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252					
Dim Min		Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1 5.21 –		_			
е	_	_	2.286		
Е	6.45	6.70	6.58		
E1	4.32				
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	_		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	11.6			
X1	1.5			
X2	7.0			
Y1	2.5			
Y2	7.0			
С	6.9			
F1	23			



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